

EE 466/586
VLSI Design

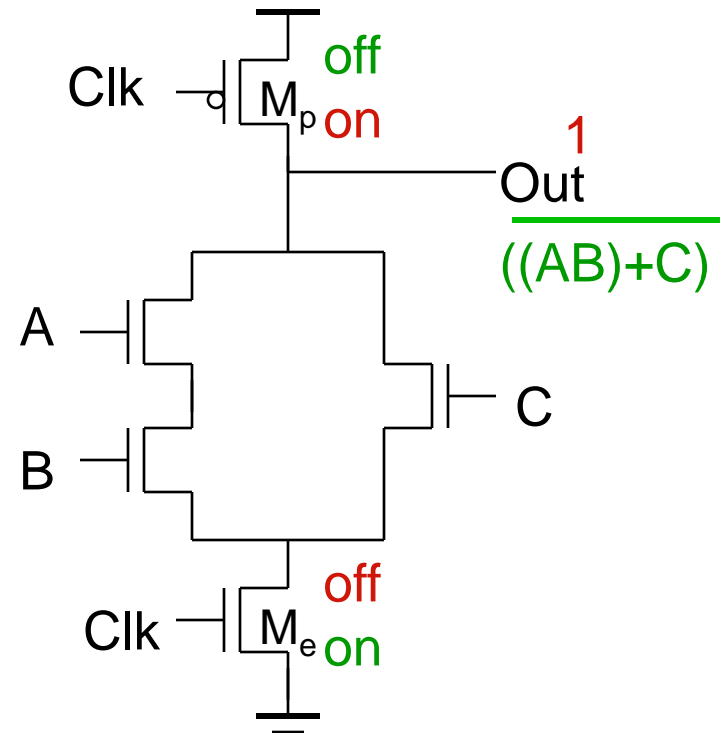
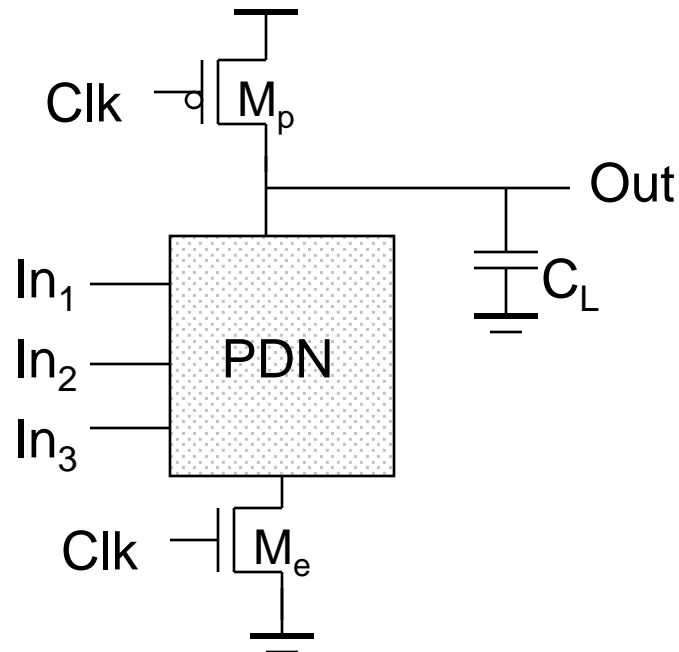
Partha Pande
School of EECS
Washington State University
pande@eecs.wsu.edu

Lecture 15
Dynamic Logic

Dynamic CMOS

- In **static** circuits at every point in time (except when switching) the output is connected to either GND or V_{DD} via a low resistance path.
 - fan-in of n requires $2n$ (n N-type + n P-type) devices
- **Dynamic** circuits rely on the temporary storage of signal values on the capacitance of high impedance nodes.
 - requires on $n + 2$ ($n+1$ N-type + 1 P-type) transistors

Dynamic Gate



Two phase operation

Precharge ($\text{Clk} = 0$)

Evaluate ($\text{Clk} = 1$)

Conditions on Output

- ❑ Once the output of a dynamic gate is discharged, it cannot be charged again until the next precharge operation.
- ❑ Inputs to the gate can make **at most** one transition during evaluation.
- ❑ Output can be in the high impedance state during and after evaluation (PDN off), state is stored on C_L
- ❑ This behavior is fundamentally different than the static counterpart that always has a low resistance path between the output and one of the power rails.

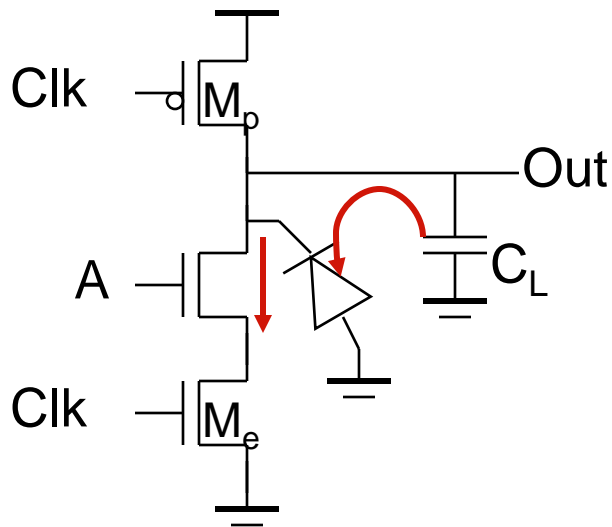
Properties of Dynamic Gates

- ❑ Logic function is implemented by the PDN only
 - number of transistors is $N + 2$ (versus $2N$ for static complementary CMOS)
- ❑ Full swing outputs ($V_{OL} = \text{GND}$ and $V_{OH} = V_{DD}$)
- ❑ Non-ratioed - sizing of the devices does not affect the logic levels
- ❑ Faster switching speeds
 - reduced load capacitance due to **lower input** capacitance (C_{in})
 - reduced load capacitance due to smaller output loading (C_{out})
 - no I_{sc} , so all the current provided by PDN goes into discharging CL

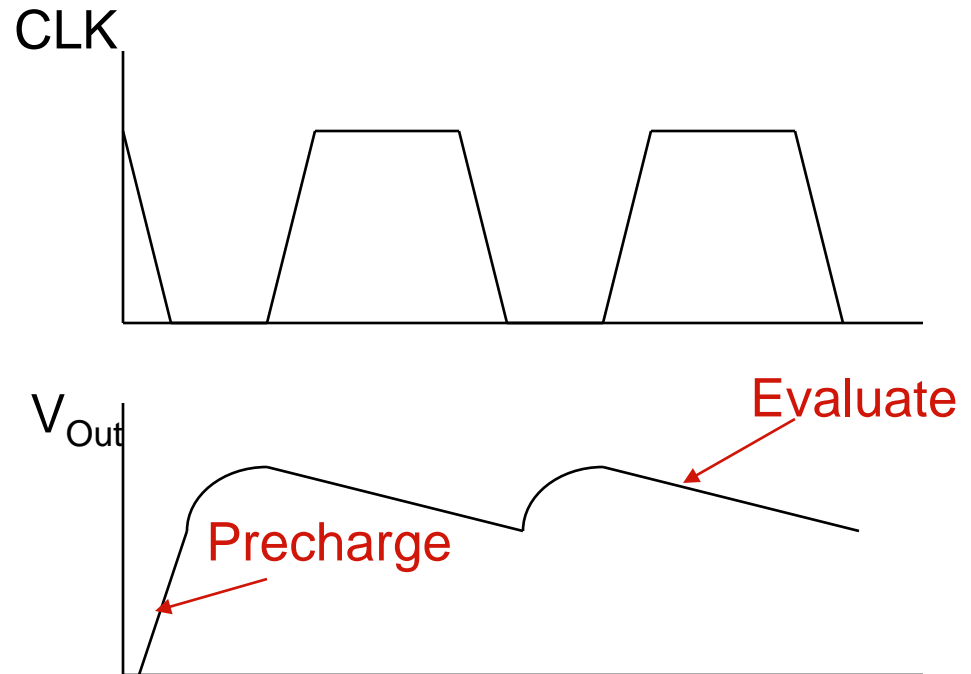
Properties of Dynamic Gates

- ❑ Overall power dissipation usually **higher** than static CMOS
 - no static current path ever exists between V_{DD} and GND
 - no glitching
 - **higher transition probabilities**
 - **extra load on Clk**
- ❑ Needs a precharge/evaluate clock

Issues in Dynamic Design 1: Charge Leakage

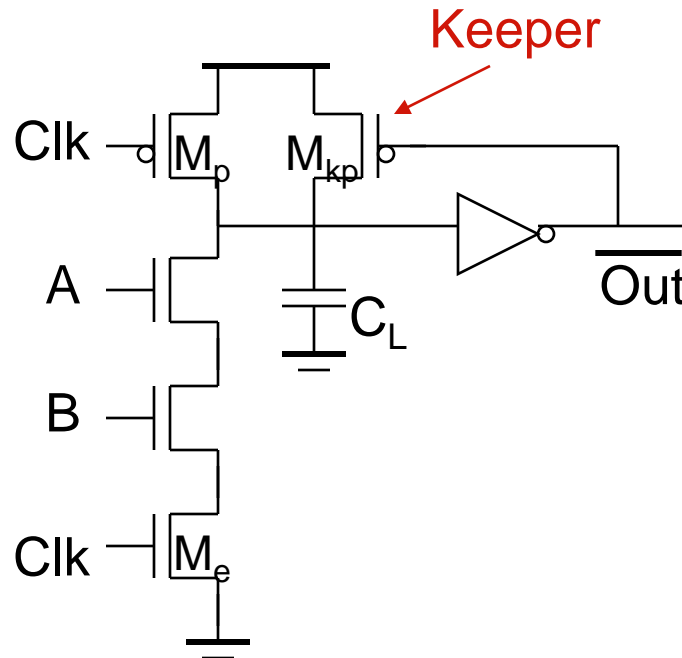


Leakage sources



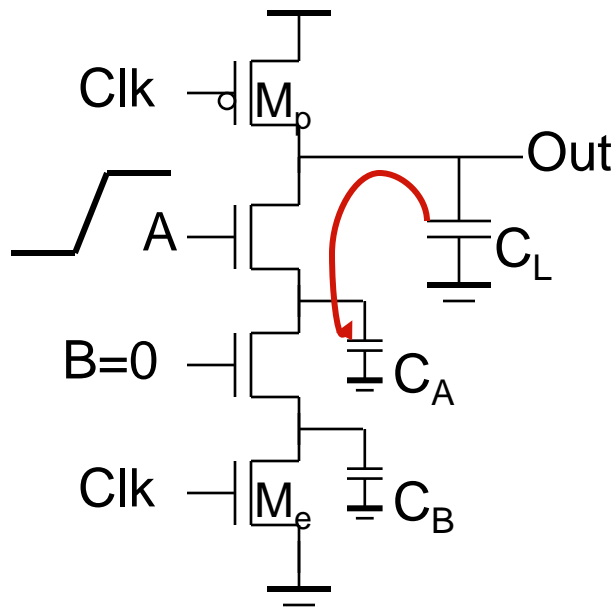
leakage sources are reverse-biased diode and the sub-threshold leakage of the NMOS pull down device.

Solution to Charge Leakage



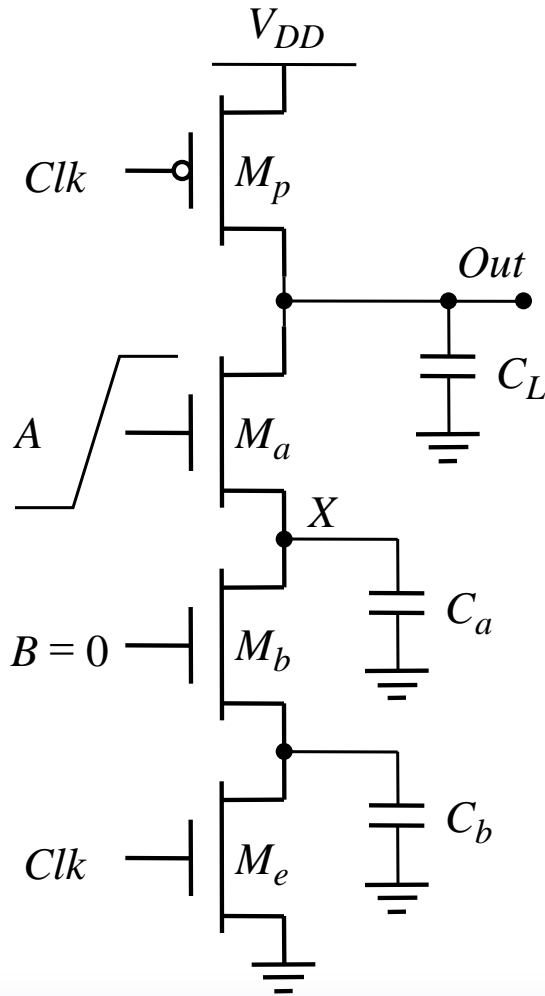
Same approach as level restorer for pass-transistor logic
During precharge, Out is VDD and inverter out is GND ,
so keeper is on

Issues in Dynamic Design 2: Charge Sharing



Charge stored originally on C_L is redistributed (shared) over C_L and C_A leading to reduced robustness
CA initially discharged and CL fully charged

Charge Sharing



case 1) if $\Delta V_{out} < V_{Tn}$

$$C_L V_{DD} = C_L V_{out}(t) + C_a (V_{DD} - V_{Tn}(V_X))$$

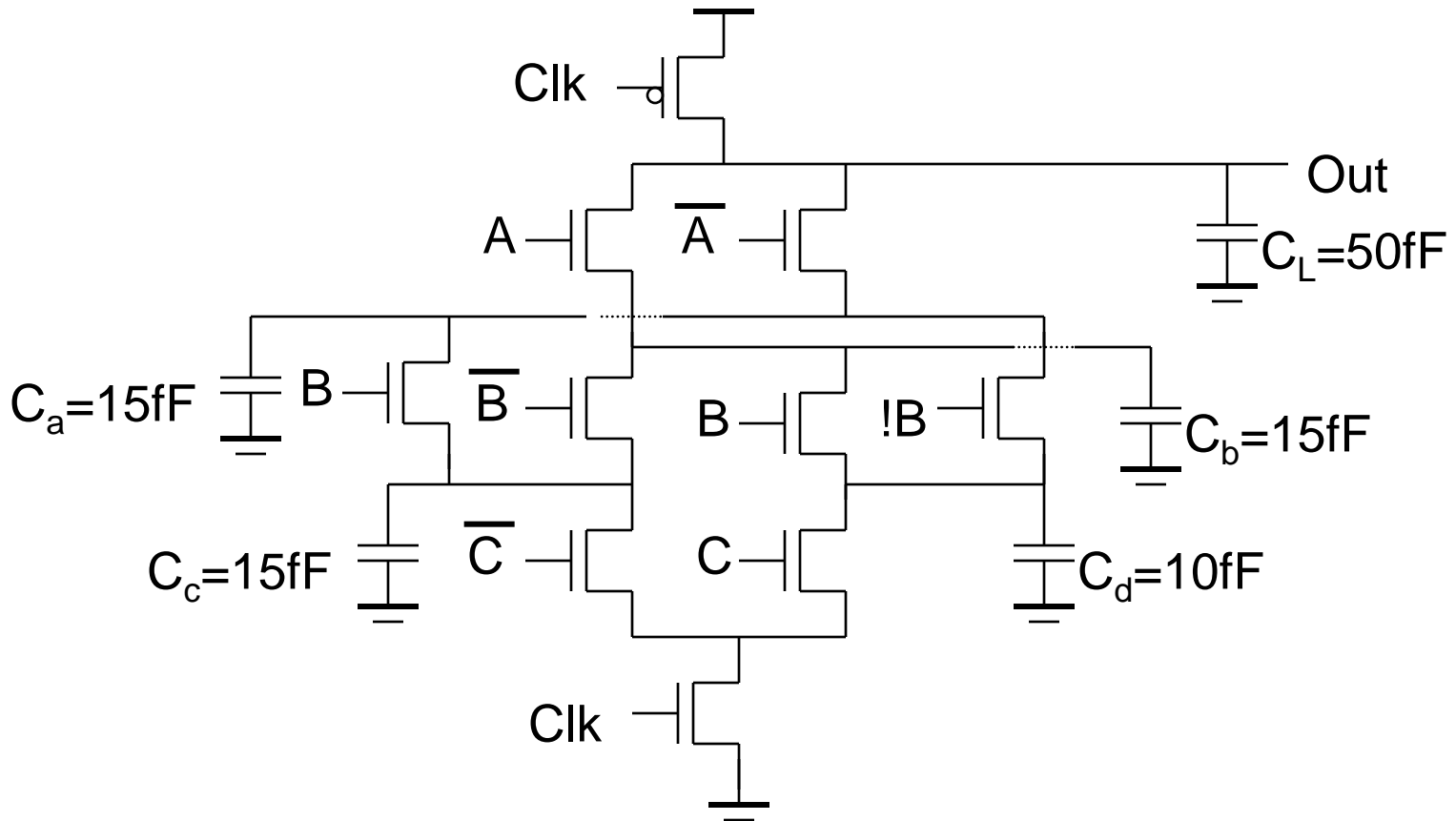
or

$$\Delta V_{out} = V_{out}(t) - V_{DD} = -\frac{C_a}{C_L} (V_{DD} - V_{Tn}(V_X))$$

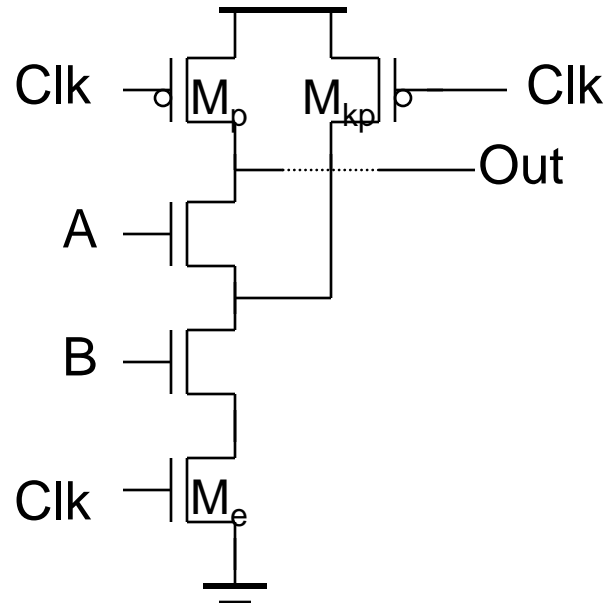
case 2) if $\Delta V_{out} > V_{Tn}$

$$\Delta V_{out} = -V_{DD} \left(\frac{C_a}{C_a + C_L} \right)$$

Charge Sharing Example

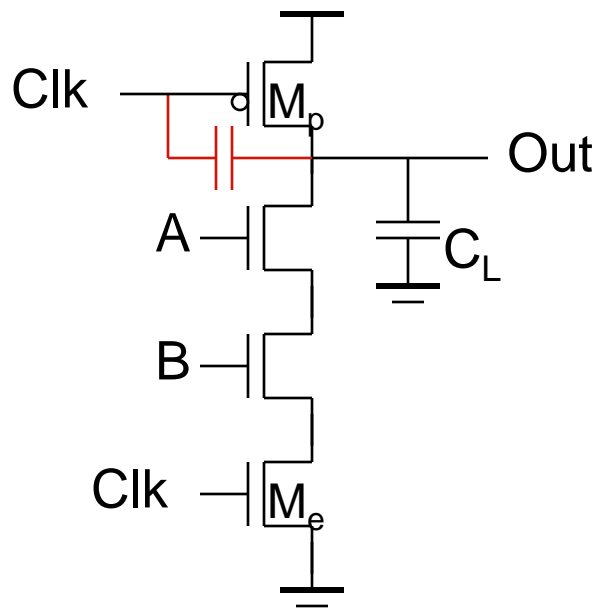


Solution to Charge Redistribution



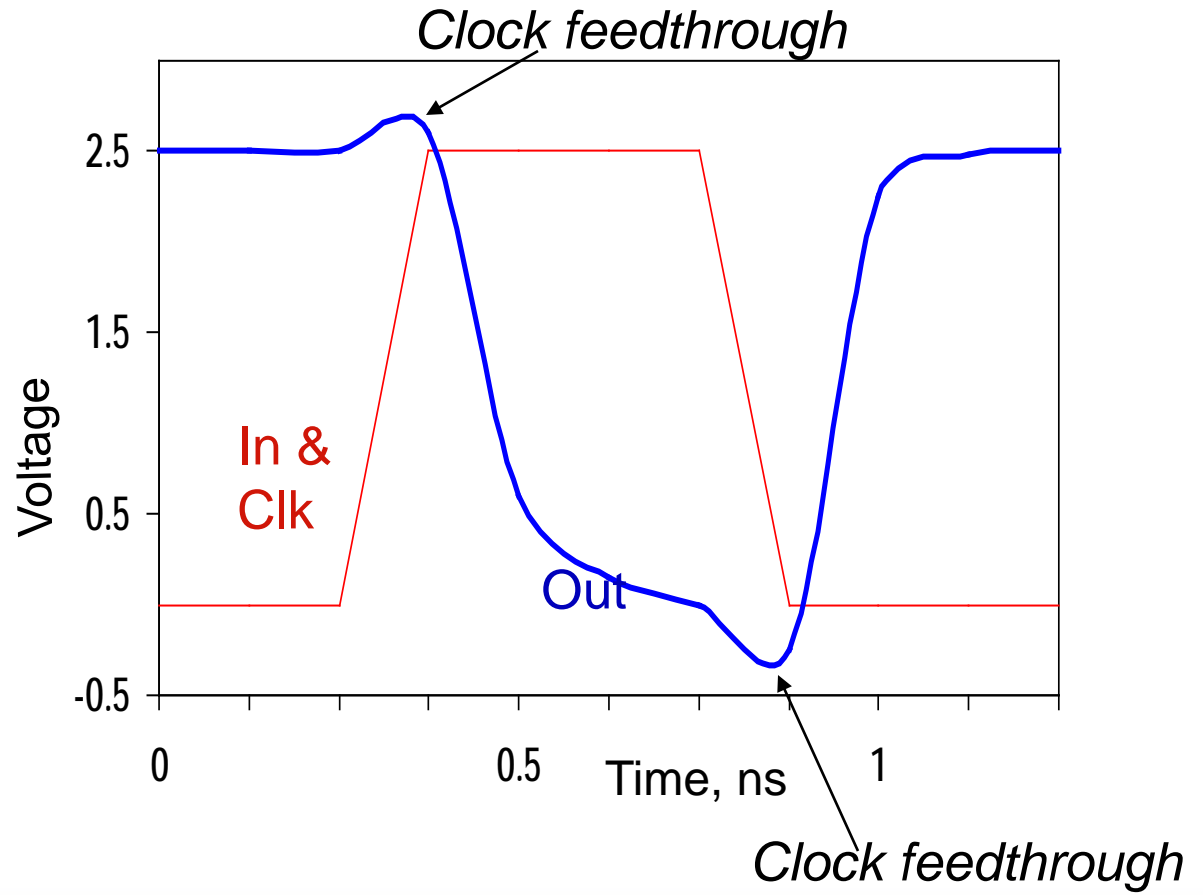
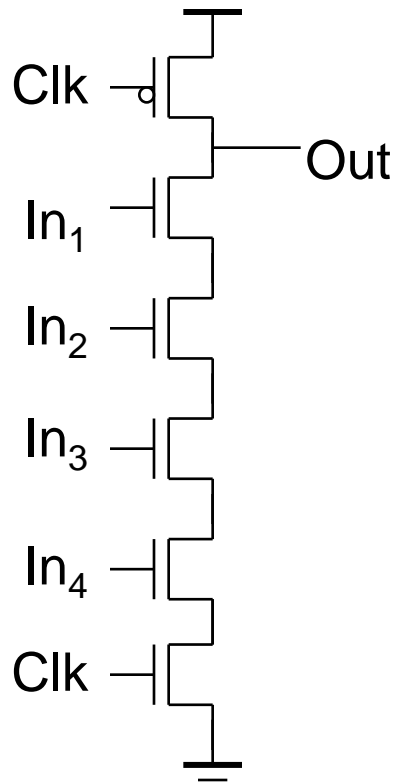
Precharge internal nodes using a clock-driven transistor
(at the cost of increased area and power)

Issues in Dynamic Design 3: Clock Feedthrough

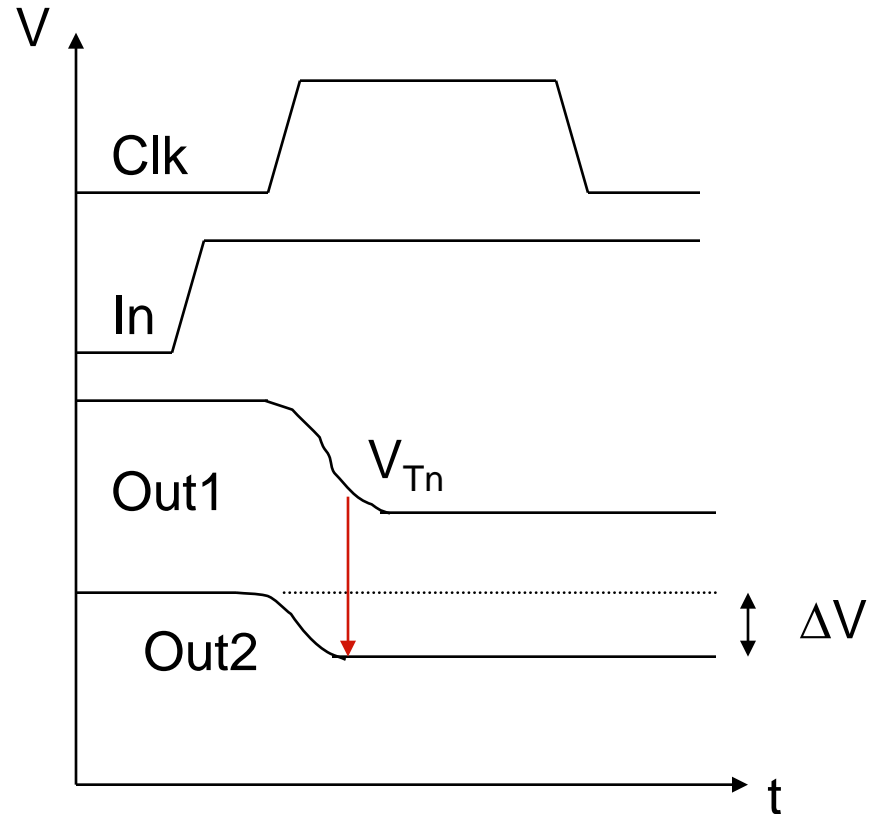
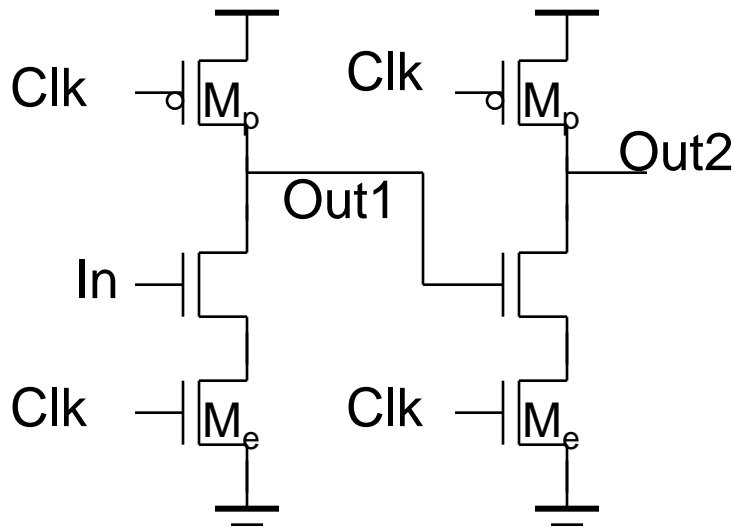


Coupling between Out and Clk input of the precharge device due to the gate to drain capacitance. So voltage of Out can rise above V_{DD} . The fast rising (and falling edges) of the clock **couple** to Out.

Clock Feedthrough



Cascading Dynamic Gates

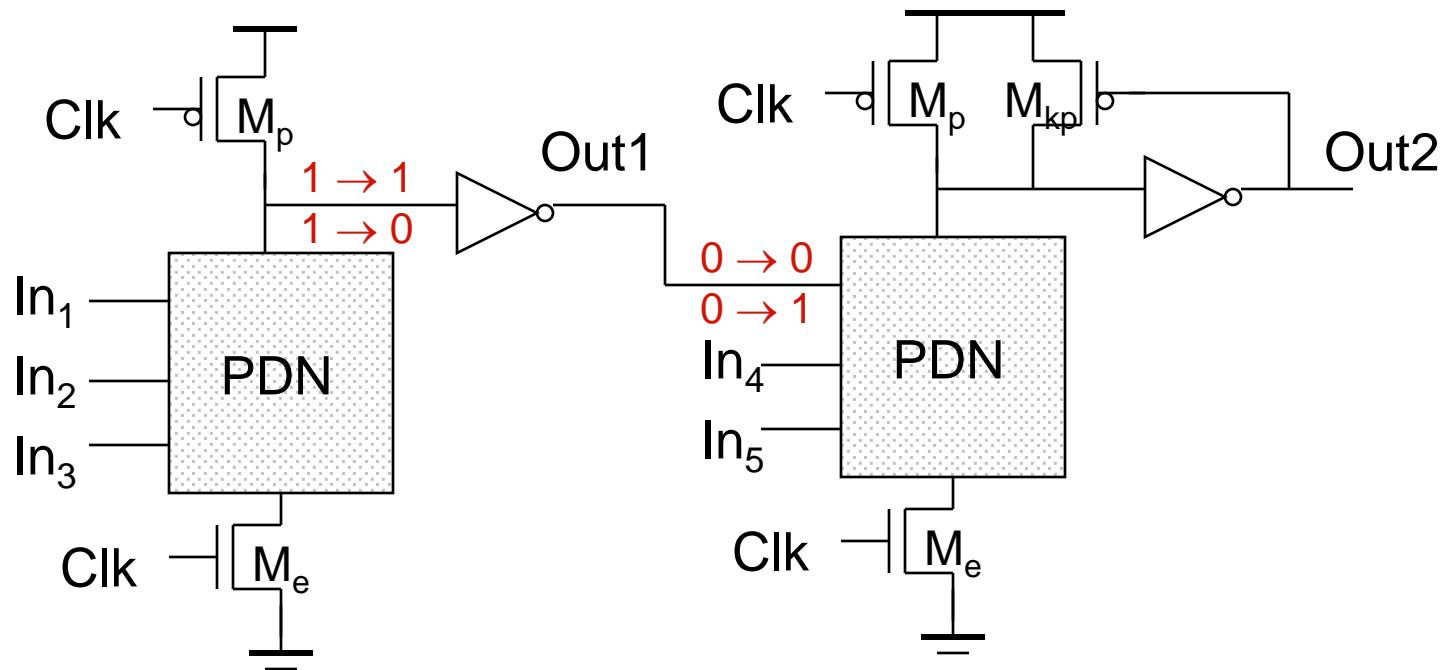


Only 0 \rightarrow 1 transitions allowed at inputs!

Cascading Dynamic Gates

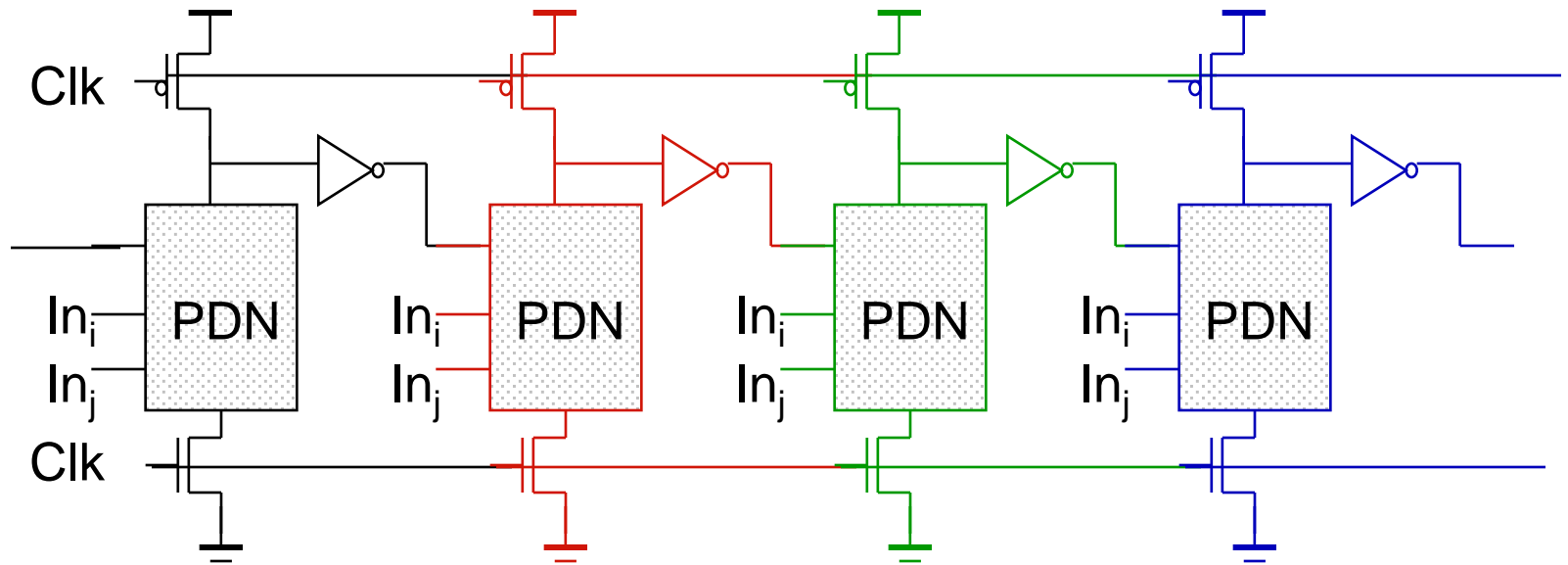
- ❑ Out2 should remain at V_{DD} since Out1 transitions to 0 during evaluation. However, since there is a finite propagation delay for the input to discharge Out1 to GND, the second output also starts to discharge.
- ❑ The second dynamic inverter turns off (PDN) when Out1 reaches V_{Tn} .
- ❑ Setting all inputs of the second gate to 0 during precharge will fix it.
- ❑ Correct operation is guaranteed (ignoring charge redistribution and leakage) as long as the inputs can only make a single 0 \rightarrow 1 transition during the evaluation period

Domino Logic



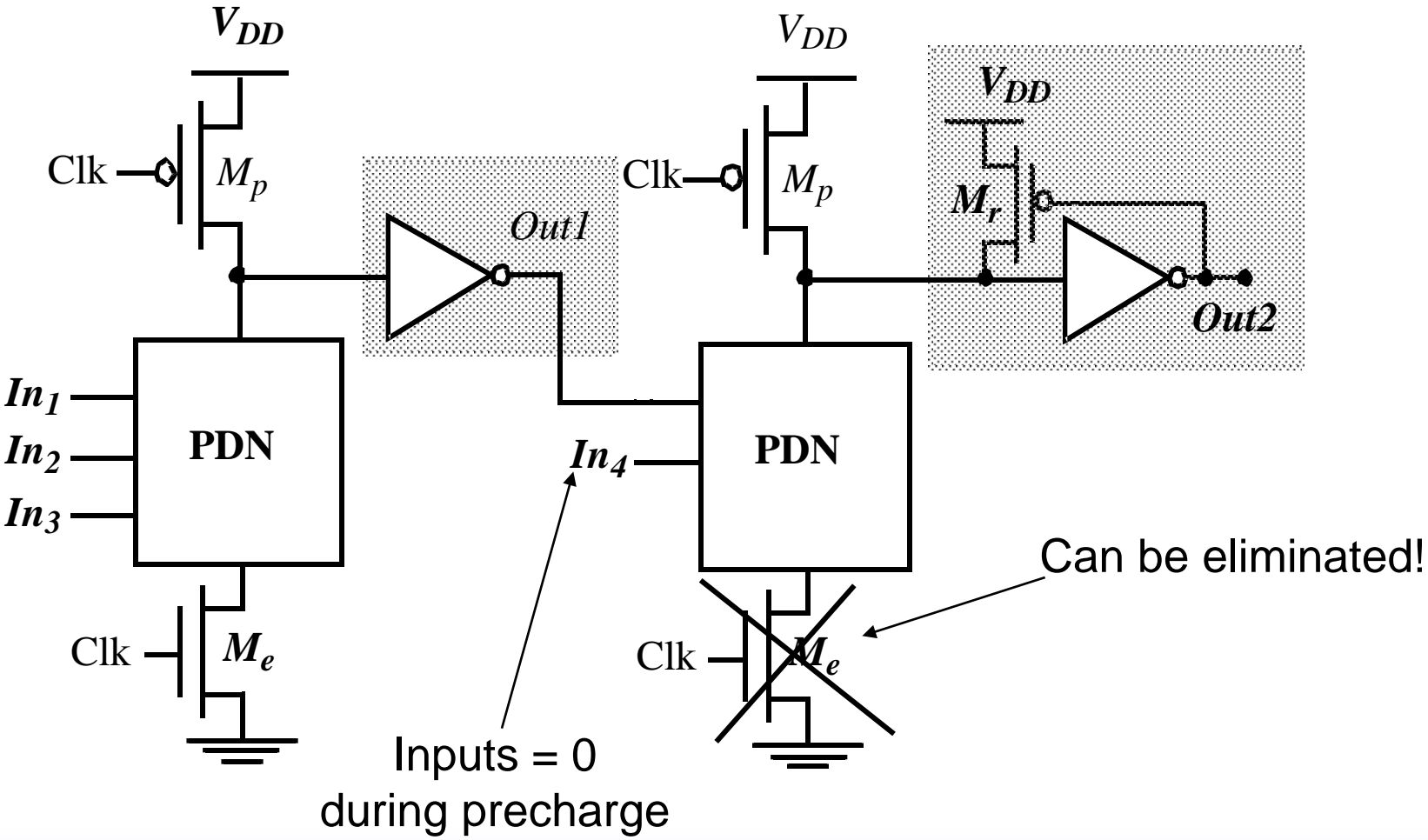
Ensures all inputs to the Domino gate are set to 0 at the end of the precharge period. Hence, the only possible transition during evaluation is 0 -> 1

Why Domino?

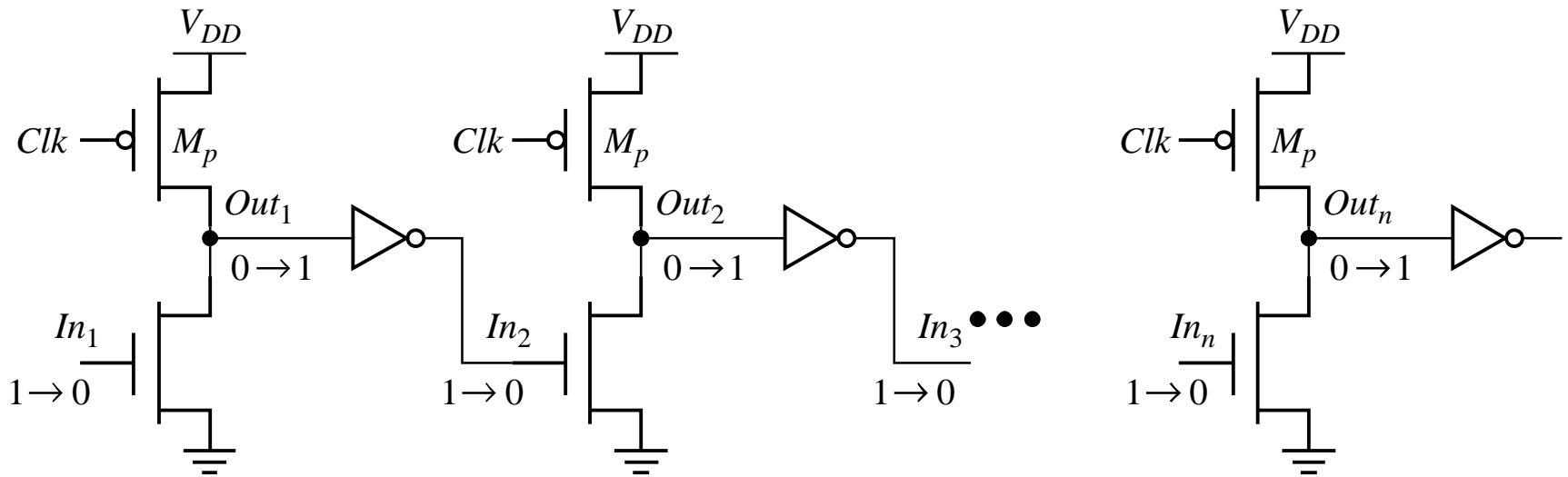


Like falling dominos!

Designing with Domino Logic

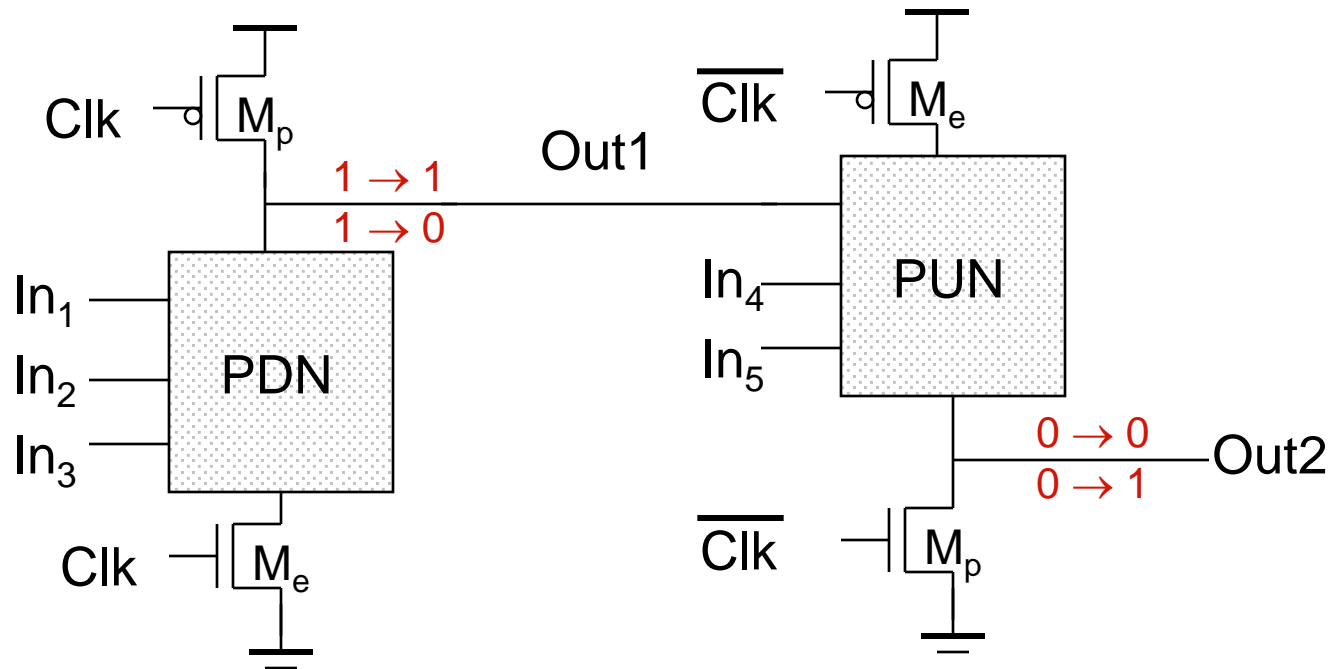


Footless Domino



The first gate in the chain needs a foot switch
Precharge is rippling – short-circuit current
A solution is to delay the clock for each stage

np-CMOS

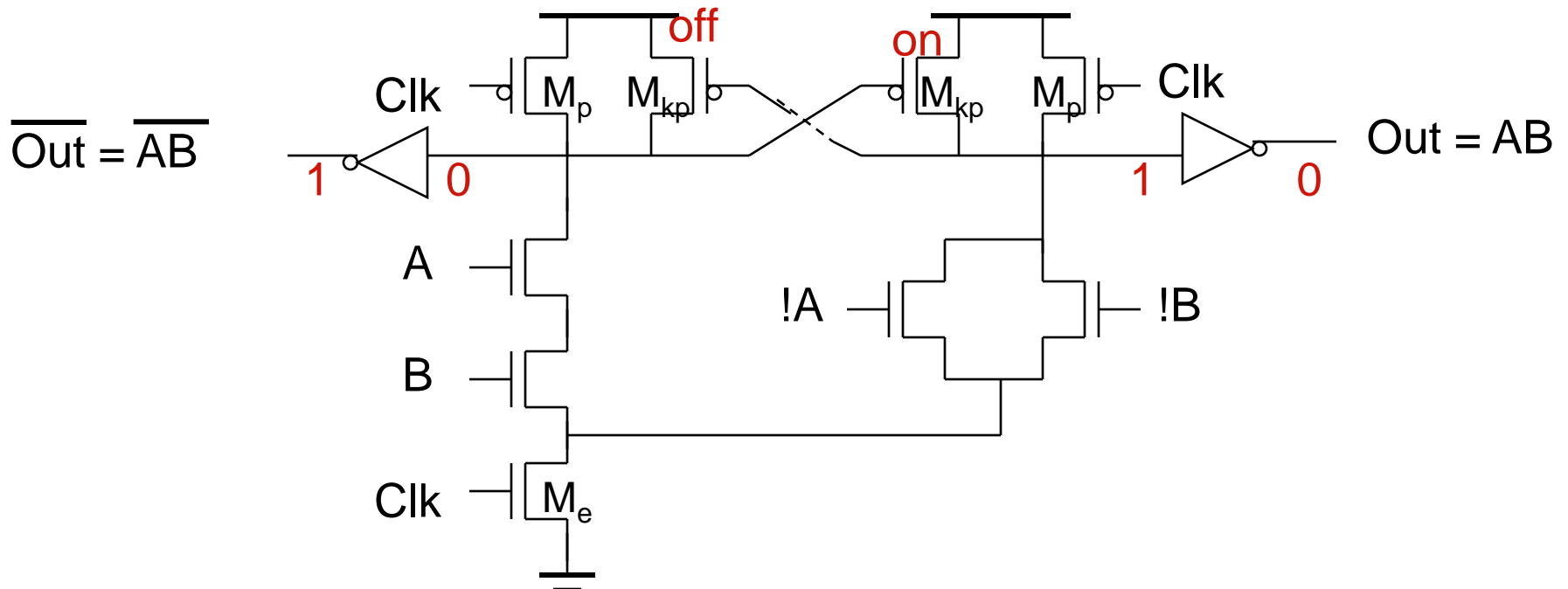


Only $0 \rightarrow 1$ transitions allowed at inputs of PDN
Only $1 \rightarrow 0$ transitions allowed at inputs of PUN

Properties of Domino Logic

- Only non-inverting logic can be implemented
- Very high speed
 - static inverter can be skewed, only L-H transition
 - Input capacitance reduced

Differential (Dual Rail) Domino



Solves the problem of non-inverting logic

Take Home Exercise

- Design a dual-rail XOR/XNOR domino gate and share as many transistors as possible between the true and complement logic blocks